

9097250 TOSHIBA (DISCRETE/OPTO)

560 07429 07-33-09

2SC790

SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

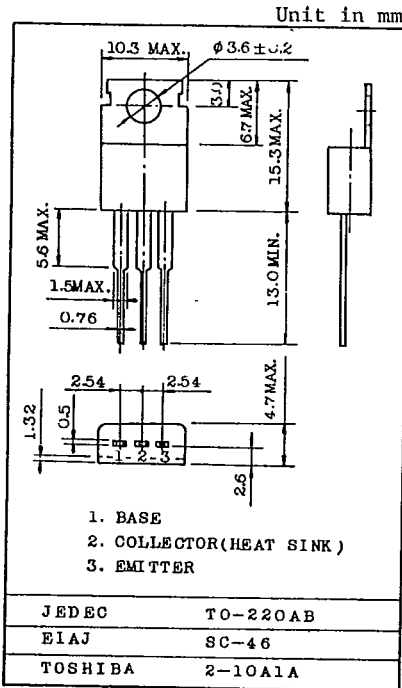
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- Complementary to 2SA490.
- Recommended for 10W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	3	A
Emitter Current	I _E	-3	A
Collector Power Dissipation (Tc=25°C)	P _C	25	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =30V, I _E =0	-	-	10	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} =5V, I _C =0	-	-	100	μA
Collector-Emitter Breakdown Voltage	V(BR)CBO	I _C =50mA, I _B =0	40	-	-	V
Emitter-Base Breakdown Voltage	V(BR)EBO	I _E =10mA, I _C =0	5	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =2V, I _C =0.5A	40	-	240	
	h _{FE} (2)	V _{CE} =2V, I _C =2A	13	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =2A, I _B =0.2A	-	0.25	1.4	V
Base-Emitter Voltage	V _{BE}	V _{CE} =2V, I _C =2A	-	0.85	1.8	V
Transition Frequency	f _T	V _{CE} =2V, I _C =0.5A	3	10	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	85	-	pF

Note: h_{FE}(1) Classification R : 40 ~ 80, O : 70 ~ 140, Y : 120 ~ 240

TOSHIBA CORPORATION